

## SEMICONDUCTOR TECHNICAL DATA

# KTC8550 EPITAXIAL PLANAR PNP TRANSISTOR

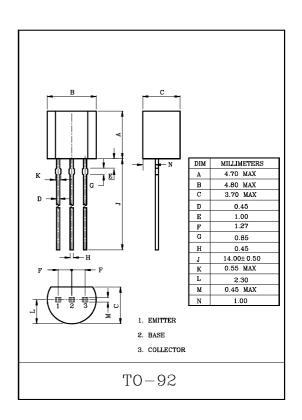
### HIGH CURRENT APPLICATION.

#### FEATURE

· Complementary to KTC8050.

#### MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	$V_{CBO}$	-35	V	
Collector-Emitter Voltage	$V_{\text{CEO}}$	-30	V	
Emitter-Base Voltage	$V_{EBO}$	-5	V	
Collector Current	$I_{\rm C}$	-800	mA	
Emitter Current	$I_{\mathrm{E}}$	800	mA	
Collector Power Dissipation	Pc	625	mW	
Junction Temperature	T <sub>j</sub>	150	${\mathbb C}$	
Storage Temperature Range	$T_{\mathrm{stg}}$	-55~150	$^{\circ}$	



#### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{\mathrm{CBO}}$	$V_{CB}$ =-15V, $I_{E}$ =0	-	-	-50	nA
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	$I_{\rm C}$ =-0.5mA, $I_{\rm E}$ =0	-35	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_C$ =-1mA, $I_B$ =0	-30	=	-	V
DC Current Gain	h <sub>FE</sub> (1) (Note)	$V_{CE}$ =-1V, $I_{C}$ =-50mA	100	-	300	
	h <sub>FE</sub> (2)	$V_{CE}$ =-1V, $I_{C}$ =-350mA	60	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{C}$ =-500mA, $I_{B}$ =-50mA	-	-	-0.5	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -1V$ , $I_{C} = -500 \text{mA}$	_	-	-1.2	V
Transition Frequency	$\mathbf{f}_{\mathrm{T}}$	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}$ =-10V, f=1MHz, $I_{E}$ =0	_	19	_	pF

Note:  $h_{FE}(1)$  Classification  $C: 100 \sim 200$ ,  $D: 150 \sim 300$ 

